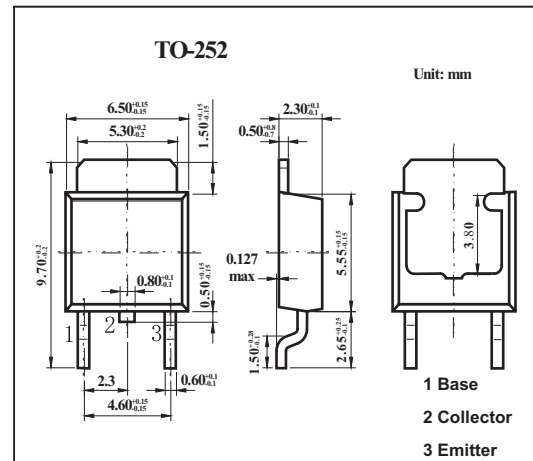


Silicon PNP Transistor

2SA1923

■ Features

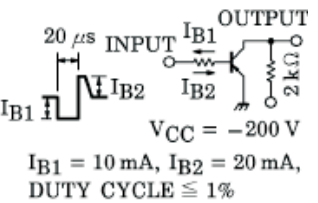
- High Voltage: $V_{CBO} = -400V$
- Low Saturation Voltage: $V_{CE(sat)} = -1V(\text{Max.})$
 $I_C = -100mA, I_B = -10mA$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-to-Base Voltage	V_{CBO}	-400	V
Collector-to-Emitter Voltage	V_{CEO}	-400	V
Emitter-to-Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-0.5	A
Collector Current (Pulse)	I_{CP}	-1	A
Base Current	I_B	-0.25	A
Collector Dissipation $T_c = 25^\circ C$	P_C	1	W
		10	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-400V, I _E =0			-10	μA
Emitter Cutoff Current	IEBO	V _{EB} =-7V, I _C =0			-1	μA
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-400			V
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-20mA	140		450	
		V _{CE} =-5V, I _C =-100mA	140		400	
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-0.4	-1.0	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA		-0.76	-0.9	V
Transition Frequency	f _T	V _{CE} =-5V, I _C =-50mA		35		MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz, I _E =0		18		pF
Switching Time Turn-on Time	ton	 20 μs INPUT I_{B1} OUTPUT I_{B2} I_{B2} 2kΩ V_{CC} = -200 V I_{B1} = 10 mA, I_{B2} = 20 mA, DUTY CYCLE ≤ 1%		0.2		μs
Switching Time Storage Time	tstg			2.3		μs
Switching Time Fall Time	tf			0.2		μs